

## GaAs Schottky Diode

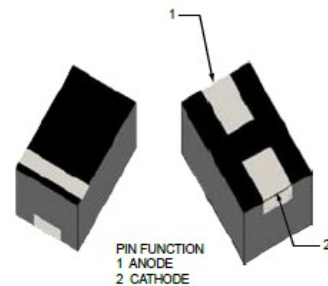
Rev. V1

### Features

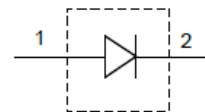
- Small Footprint, only 50 x 30 mils.
- Very Low Parasitic Package Inductance, Series Resistance, and Low Package Capacitance
- RoHS\* Compliant

### Description

The SMGS11 is a GaAs Schottky diode in a molded plastic DFN package. It is designed for broadband detector and single diode mixer. It is in single configuration. It has a high cutoff frequency and can be used beyond 26.5 GHz.



Case 0503 - Molded Plastic DFN Package



### Electrical Specifications: $T_A = +25^\circ\text{C}$

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Forward Voltage ( $V_F$ )	$I_R = 1 \text{ mA}$	V	620	—	760
Total Capacitance ( $C_T$ )	$V_R = 0 \text{ V}, 1 \text{ MHz}$ $V = 0 \text{ V}, >4 \text{ GHz}$	pF	—	0.10 0.08	0.13 0.10
Series Resistance ( $R_S$ )	$I_F = 5 \text{ mA}$	$\Omega$	—	—	7
Video Resistance ( $R_V$ )	$I_F = 40 \mu\text{A}$	$\Omega$	—	1250	—
Tangential Signal Sensitivity ( $T_{SS}$ )	NF -3 dB, 10 GHz	dBm	—	-57	—
Voltage Sensitivity ( $\gamma$ )	$P_{IN} = -30 \text{ dBm}$ , Video BW = 500 KHz, 10 GHz	mV/mW	—	8000	—

### Absolute Maximum Ratings

Parameter	Absolute Maximum
Input Power	20 dBm
Reverse Voltage	5 V
Forward Current	20 mA
Junction Temperature	+175°C
Storage Temperature	-65°C to +150°C
Solder Temperature	+260°C, peak for 5 sec, per JEDEC J-STD-20C

### Handling Procedures

Please observe the following precautions to avoid damage:

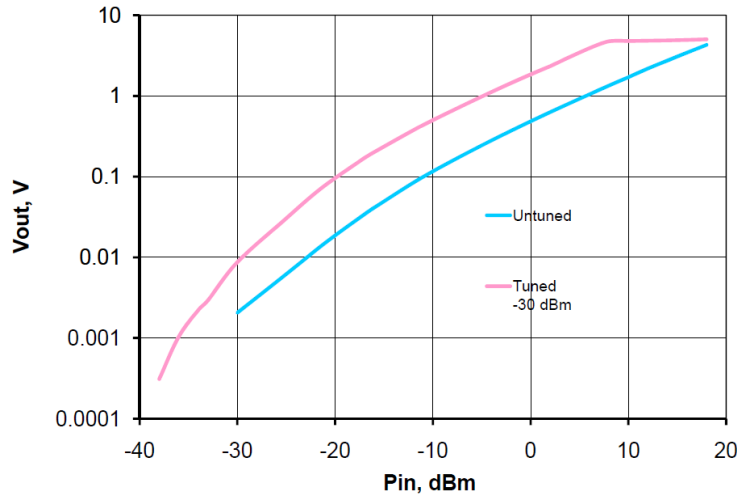
### Static Sensitivity

These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these (HBM) Class 0 devices.

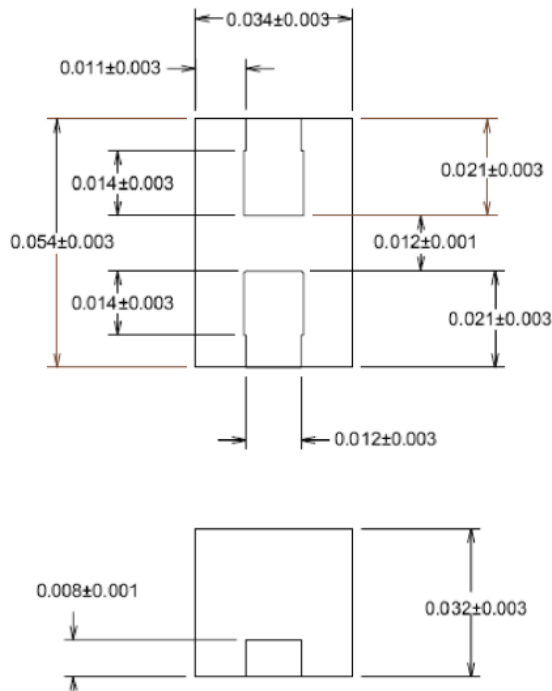
1 \* Restrictions on Hazardous Substances, European Union Directive 2011/65/EU.

### Typical Dynamic Transfer Characteristics: $R_L = 10\ \text{m}\Omega$ , $F_O = 10\ \text{GHz}$

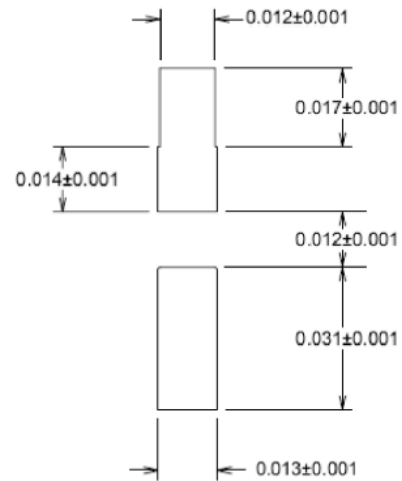
Output Voltage vs. Input Power



### Lead-Free 0503 Plastic DFN Package



### Soldering Footprint



All Dimensions +/-0.001 Inch